## **Supplementary Information for**

## The rectifying and negative differential resistance effects in heterojunctions of graphene/h-BN nanoribbons

Yipeng An,\*a Mengjun Zhang,a Dapeng Wu,b Tianxing Wang,a Zhaoyong Jiao,a Congxin Xia,a Zhaoming Fuac and Kun Wangd

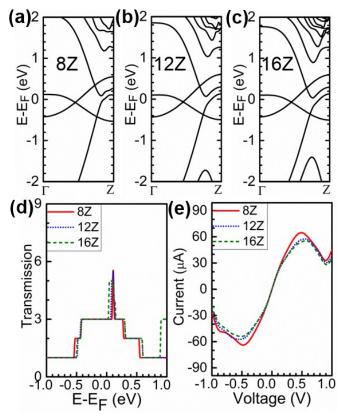
<sup>a</sup>College of Physics and Materials Science, Henan Normal University, Xinxiang 453007, China.

E-mail address: ypan@htu.edu.cn.

<sup>b</sup>School of Chemistry and Chemical Engineering, Henan Normal University, Xinxiang 453007, China

<sup>c</sup>Beijing National Laboratory for Condensed Matter Physics, Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China

<sup>d</sup>Department of Physics and Astronomy & NanoSEC, University of Georgia, Athens, GA 30602, USA



**Fig. S1** Band structures of Gra-BNud heterojunctions with 8 (a), 12 (b), and 16 (c) zigzag chains. (d) and (e) refer to the transmission spectra and *I–V* curves of Gra-BNud heterojunctions with different widths.

The Gra-BNud heterojunctions with larger widths have the very similar band structures, transmission spectra, and I-V curves.